

BF421, BF423

High Voltage Transistors

PNP Silicon



ON Semiconductor®

<http://onsemi.com>

MAXIMUM RATINGS

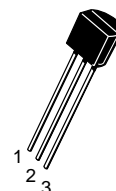
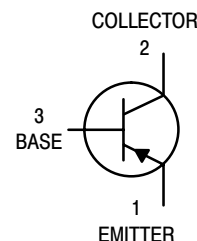
Rating	Symbol	BF421	BF423	Unit
Collector–Emitter Voltage	V_{CEO}	–300	–250	Vdc
Collector–Base Voltage	V_{CBO}	–300	–250	Vdc
Emitter–Base Voltage	V_{EBO}	–5.0		Vdc
Collector Current – Continuous	I_C	–50		mAdc
Collector Current – Peak	I_{CM}	100		mA
Total Device Dissipation (Note 1) @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	830 6.6		mW mW/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	–55 to +150		°C

THERMAL CHARACTERISTICS

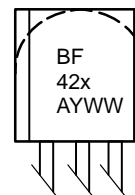
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	150	°C/W
Thermal Resistance, Junction to Lead	$R_{\theta JL}$	68	°C/W

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

1. Mounted on a FR4 board with 200 mm² of 1 oz copper and lead length of 5 mm.



MARKING DIAGRAM



TO-92 (TO-226AA)
CASE 29-11,
STYLE 14

x = 1 or 3
A = Assembly Location
Y = Year
WW = Work Week

ORDERING INFORMATION

Device	Package	Shipping
BF421ZL1	TO-92	2000 Ammo Pack
BF423	TO-92	5000 Units/Box
BF423ZL1	TO-92	2000 Ammo Pack

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ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
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OFF CHARACTERISTICS

Collector–Emitter Breakdown Voltage (Note 2) ($I_C = -1.0\text{ mA}$, $I_B = 0$)	BF421 BF423	$V_{(BR)CEO}$	-300 -250	— —	Vdc
Collector–Base Breakdown Voltage ($I_C = -100\text{ }\mu\text{A}$, $I_E = 0$)	BF421 BF423	$V_{(BR)CBO}$	-300 -250	— —	Vdc
Emitter–Base Breakdown Voltage ($I_E = -100\text{ }\mu\text{A}$, $I_C = 0$)	BF421 BF423	$V_{(BR)EBO}$	-5.0 -5.0	— —	Vdc
Collector Cutoff Current ($V_{CB} = -200\text{ Vdc}$, $I_E = 0$)	BF421 BF423	I_{CBO}	— —	-0.01 —	μA
Emitter Cutoff Current ($V_{EB} = -5.0\text{ Vdc}$, $I_C = 0$)	BF421 BF423	I_{EBO}	— —	-100 —	nA

ON CHARACTERISTICS

DC Current Gain ($I_C = -25\text{ mA}$, $V_{CE} = -20\text{ Vdc}$)	BF421 BF423	h_{FE}	50 50	— —	—
Collector–Emitter Saturation Voltage ($I_C = -20\text{ mA}$, $I_B = -2.0\text{ mA}$)		$V_{CE(sat)}$	—	-0.5	Vdc
Base–Emitter Saturation Voltage ($I_C = -20\text{ mA}$, $I_B = -2.0\text{ mA}$)		$V_{BE(sat)}$	—	-2.0	Vdc

SMALL–SIGNAL CHARACTERISTICS

Current–Gain — Bandwidth Product ($I_C = -10\text{ mA}$, $V_{CE} = -10\text{ Vdc}$, $f = 20\text{ MHz}$)		f_T	60	—	MHz
Common Emitter Feedback Capacitance ($V_{CB} = -30\text{ Vdc}$, $I_E = 0$, $f = 1.0\text{ MHz}$)		C_{re}	—	2.8	pF

2. Pulse Test: Pulse Width $\leq 300\text{ }\mu\text{s}$; Duty Cycle $\leq 2.0\%$.

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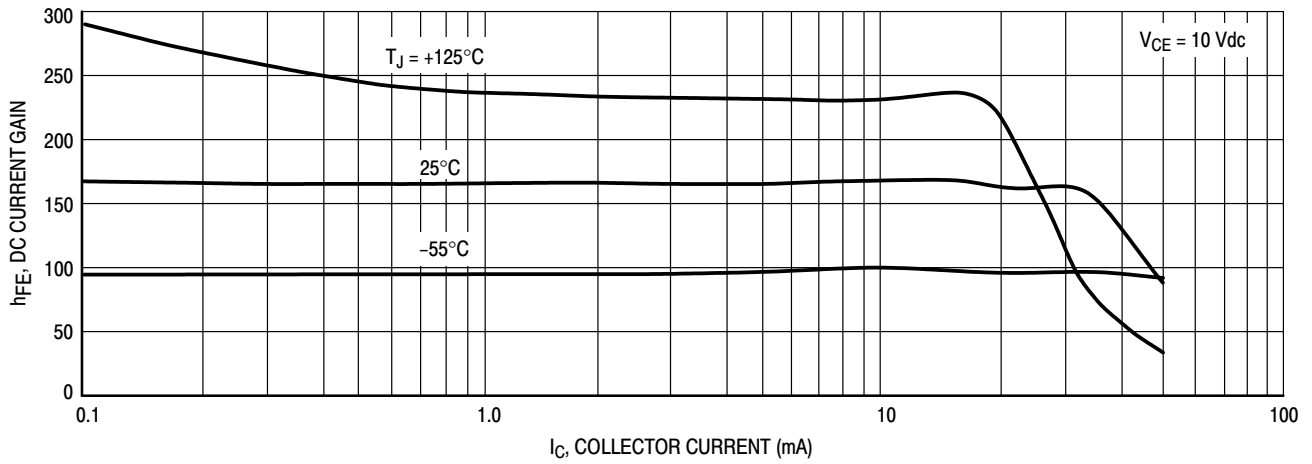


Figure 1. DC Current Gain

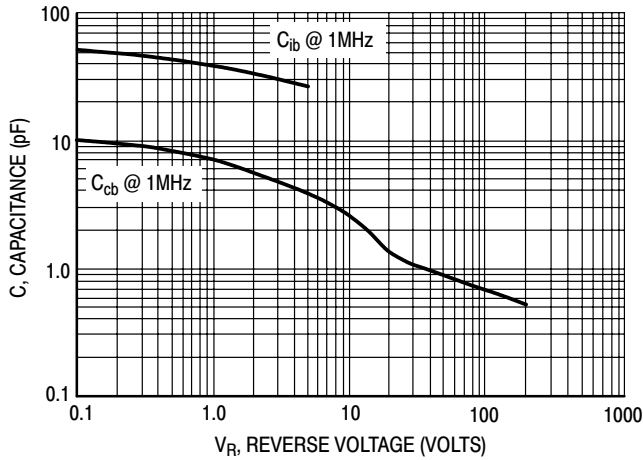


Figure 2. Capacitance

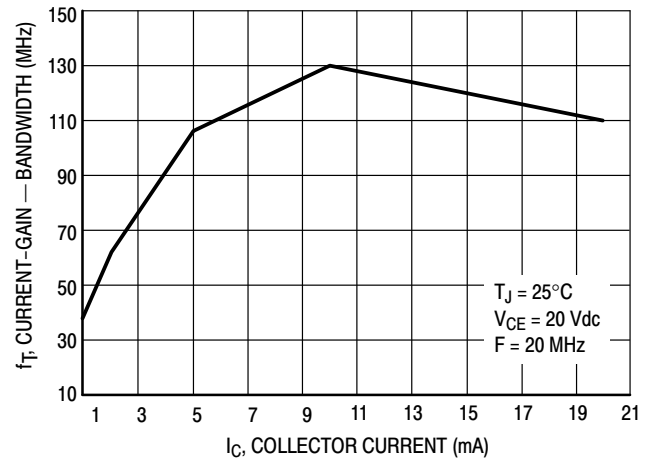


Figure 3. Current-Gain — Bandwidth

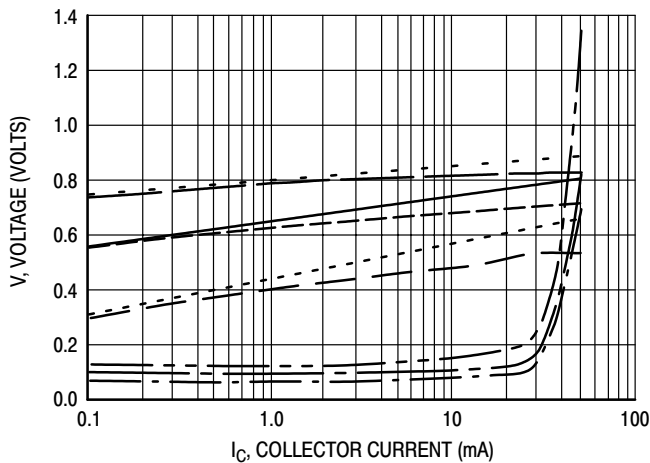


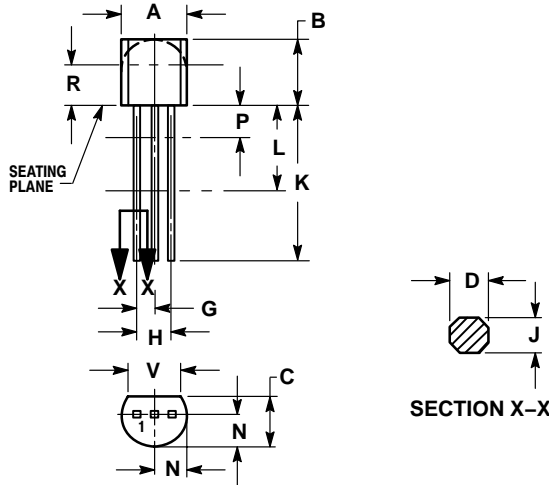
Figure 4. "ON" Voltages

- $V_{CE(sat)}$ @ 25°C , $I_C/I_B = 10$
- - $V_{CE(sat)}$ @ 125°C , $I_C/I_B = 10$
- . - $V_{CE(sat)}$ @ -55°C , $I_C/I_B = 10$
- $V_{BE(sat)}$ @ 25°C , $I_C/I_B = 10$
- - $V_{BE(sat)}$ @ 125°C , $I_C/I_B = 10$
- . - $V_{BE(sat)}$ @ -55°C , $I_C/I_B = 10$
- $V_{BE(on)}$ @ 25°C , $V_{CE} = 10 \text{ V}$
- - $V_{BE(on)}$ @ 125°C , $V_{CE} = 10 \text{ V}$
- . - $V_{BE(on)}$ @ -55°C , $V_{CE} = 10 \text{ V}$

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PACKAGE DIMENSIONS

TO-92 (TO-226)
CASE 029-11
ISSUE AJ




NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.175	0.205	4.45	5.20
B	0.170	0.210	4.32	5.33
C	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
E	0.045	0.055	1.15	1.39
F	0.095	0.105	2.42	2.66
G	0.015	0.020	0.39	0.50
H	0.500	---	12.70	---
I	0.250	---	6.35	---
J	0.080	0.105	2.04	2.66
K	---	0.100	---	2.54
L	0.115	---	2.93	---
M	0.135	---	3.43	---

STYLE 14:

1. EMITTER
2. COLLECTOR
3. BASE

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